

info@atrinelec.com



@atrinelec



TOSHIBA

TLP250

Transistor Inverter Inverter For Air Conditionor **IGBT Gate Drive** Power MOS FET Gate Drive

The TOSHIBA TLP250 consists of a GaAlAs light emitting diode and a integrated photodetector. This unit is 8-lead DIP package. TLP250 is suitable for gate driving circuit of IGBT or power MOS FET.

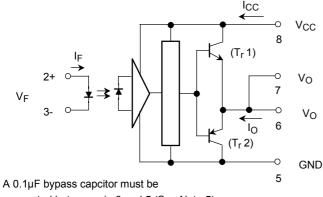
- Input threshold current: IF=5mA(max.) •
- Supply current (ICC): 11mA(max.)
- Supply voltage (V_{CC}): 10–35V
- Output current (I_O): ±1.5A (max.)
- Switching time (tpLH/tpHL): 1.5µs(max.)
- Isolation voltage: 2500V_{rms}(min.)
- UL recognized: UL1577, file No.E67349
- Option (D4) type

VDE approved: DIN VDE0884/06.92, certificate No.76823 Maximum operating insulation voltage: 630VPK Highest permissible over voltage: 4000VPK

(Note) When a VDE0884 approved type is needed, please designate the "option (D4)"

Creepage distance: 6.4mm(min.) Clearance: 6.4mm(min.)

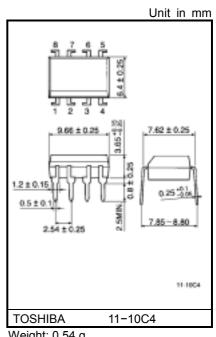
Schmatic



connected between pin 8 and 5 (See Note 5).

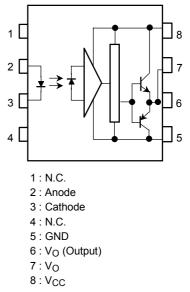
Truth Table

		Tr1	Tr2
Input LED	On	On	Off
	Off	Off	On



Weight: 0.54 g

Pin Configuration (top view)



Absolute Maximum Ratings (Ta = 25°C)

	Characteristic	Symbol	Rating	Unit	
	Forward current	١ _F	20	mA	
	Forward current derating (Ta ≥ 70°C)		ΔI _F / ΔTa	-0.36	mA / °C
LED	Peak transient forward curent	(Note 1)	I _{FPT}	1	А
	Reverse voltage		V _R	5	V
	Junction temperature	Tj	125	°C	
	"H"peak output current ($P_W \le 2.5 \mu s, f \le 15 kHz$)	(Note 2)	I _{OPH}	-1.5	А
("L"peak output current ($P_W \le 2.5 \mu s, f \le 15 kHz$)	(Note 2)	I _{OPL}	+1.5	А
	Output voltage	(Ta ≤ 70°C)	Ma	35	V
	Output voltage	(Ta = 85°C)	Vo	24	v
Detector	Currente unalte and	(Ta ≤ 70°C)	Vee	35	V
ð	Supply voltage	(Ta = 85°C)	V _{CC}	24	v
	Output voltage derating (Ta ≥ 70°C)	ΔV _O / ΔTa	-0.73	V / °C	
	Supply voltage derating (Ta \ge 70°C)		ΔV_{CC} / ΔTa	-0.73	V / °C
	Junction temperature		Tj	125	°C
Opera	ating frequency	f	25	kHz	
Opera	ating temperature range	T _{opr}	-20~85	°C	
Stora	ge temperature range	T _{stg}	-55~125	°C	
Lead	soldering temperature (10 s)	T _{sol}	260	°C	
Isolat	ion voltage (AC, 1 min., R.H.≤ 60%)	BVS	2500	Vrms	

Note 1: Pulse width $P_W \le 1\mu s$, 300pps

- Note 2: Exporenential wavefom
- Note 3: Exporenential waveform, $I_{OPH} \le -1.0A(\le 2.5\mu s)$, $I_{OPL} \le +1.0A(\le 2.5\mu s)$
- Note 4: It is 2 mm or more from a lead root.
- Note 5: Device considerd a two terminal device: Pins 1, 2, 3 and 4 shorted together, and pins 5, 6, 7 and 8 shorted together.
- Note 6: A ceramic capacitor(0.1µF) should be connected from pin 8 to pin 5 to stabilize the operation of the high gain linear amplifier. Failure to provide the bypassing may impair the switching proparty. The total lead length between capacitor and coupler should not exceed 1cm.

Recommended Operating Conditions

Characteristic		Symbol	Min.	Тур.	Max.		Unit
Input current, on	(Note 7)	I _{F(ON)}	7	8	1	10	
Input voltage, off		V _{F(OFF)}	0	_	0.8		V
Supply voltage		V _{CC}	15	_	30	20	V
Peak output current	put current		—	_	±0.5		А
Operating temperature		T _{opr}	-20	25	70	85	°C

Note 7: Input signal rise time (fall time) < 0.5 μ s.

Electrical Characteristics (Ta = -20~70°C, unless otherwise specified)

			Test					
Characteristic		Symbol	Cir– cuit	Test Condition	Min.	Тур.*	Max.	Unit
Input forward voltage		V _F	_	I _F = 10 mA , Ta = 25°C		1.6	1.8	V
Temperature coeffici forward voltage	ent of	ΔV_{F} / ΔTa	_	I _F = 10 mA	_	-2.0	_	mV / °C
Input reverse current	1	I _R	_	V _R = 5V, Ta = 25°C		_	10	μA
Input capacitance		CT	_	V = 0 , f = 1MHz , Ta = 25	5°C —	45	250	pF
Output current	"H" level	I _{OPH}	3	$V_{CC} = 30V$ $I_F = 10 \text{ m/}_{V_{8-6}} = 4V$		-1.5	_	A
	"L" level	I _{OPL}	2	(*1) $I_F = 0$ $V_{6-5} = 2.5$	5V 0.5	2	_	
Output voltage	"H" level	V _{OH}	4	$V_{CC1} = +15V, V_{EE1} = -18$ $R_L = 200\Omega, I_F = 5mA$	5V 11	12.8	_	v
Output voitage	"L" level	V _{OL}	5	V _{CC1} = +15V, V _{EE1} = -1 R _L = 200Ω, V _F = 0.8V	5V _	-14.2	-12.5	
	"H" level	Іссн	_	V _{CC} = 30V, I _F = 10mA Ta = 25°C	_	7	_	
Supply current				V _{CC} = 30V, I _F = 10mA	_	_	11	mA
Supply current	"L" level	ICCL	_	V _{CC} = 30V, I _F = 0mA Ta = 25°C	_	7.5		
				V _{CC} = 30V, I _F = 0mA	_	_	11	
Threshold input current	"Output L→H"	I _{FLH}	_	V_{CC1} = +15V, V_{EE1} = -18 R _L = 200Ω, V_O > 0V	5V _	1.2	5	mA
Threshold input voltage	"Output H→L"	I _{FHL}	_	V_{CC1} = +15V, V_{EE1} = -1 R _L = 200Ω, V_O < 0V	5V 0.8	_	_	V
Supply voltage		V _{CC}	_		10	_	35	V
Capacitance (input–output)		CS	_	V _S = 0 , f = 1MHz Ta = 25	_	1.0	2.0	pF
Resistance(input-output)		R _S	_	V _S = 500V , Ta = 25°C R.H.≤ 60%	1×10 ¹²	10 ¹⁴	_	Ω

* All typical values are at Ta = 25°C (*1): Duration of I_O time \leq 50µs

Switching Characteristics (Ta = $-20 \sim 70^{\circ}$ C, unless otherwise specified)

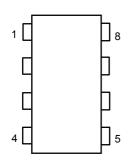
Characteristic		Symbol	Test Cir– cuit	Test Condition	Min.	Typ.*	Max.	Unit
Propagation delay time	L→H	t _{pLH}	6	I _F = 8mA (Note 7) V _{CC1} = +15V, V _{EE1} = -15V	—	0.15	0.5	
	H→L	t _{pHL}			—	0.15	0.5	
Output rise time		tr		$R_L = 200\Omega$	—	—		μs
Output fall time		t _f			—	—	-	
Common mode transient immunity at high level output		C _{MH}	7	V _{CM} = 600V, I _F = 8mA V _{CC} = 30V, Ta = 25°C	-5000	_	_	V / µs
Common mode transient immunity at low level output		C _{ML}	7	V _{CM} = 600V, I _F = 0mA V _{CC} = 30V, Ta = 25°C	5000	_	_	V / µs

* All typical values are at Ta = 25°C

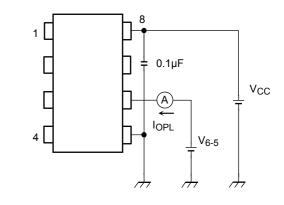
Note 7: Input signal rise time (fall time) < 0.5 μ s.

TOSHIBA

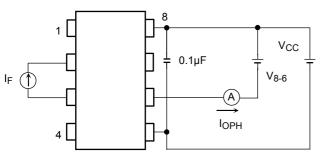
Test Circuit 1 :

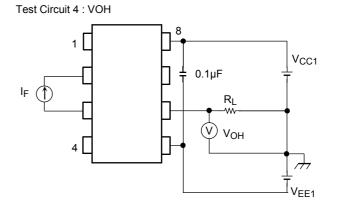


Test Circuit 2 : IOPL

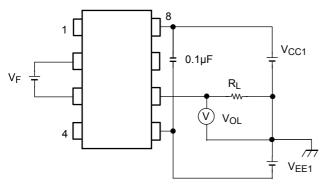


Test Circuit 3 : IOPH

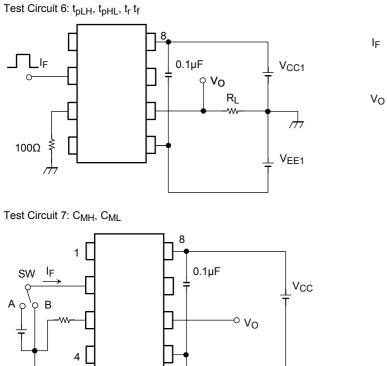


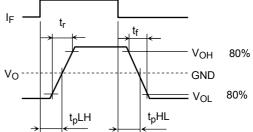


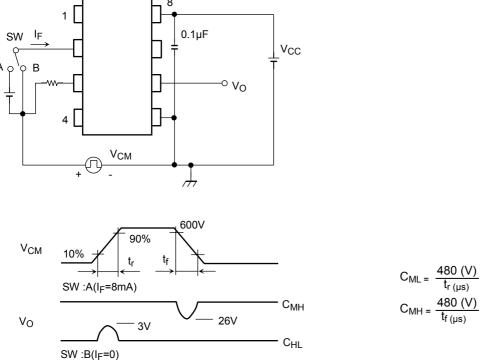
Test Circuit 5 : V_{OL}









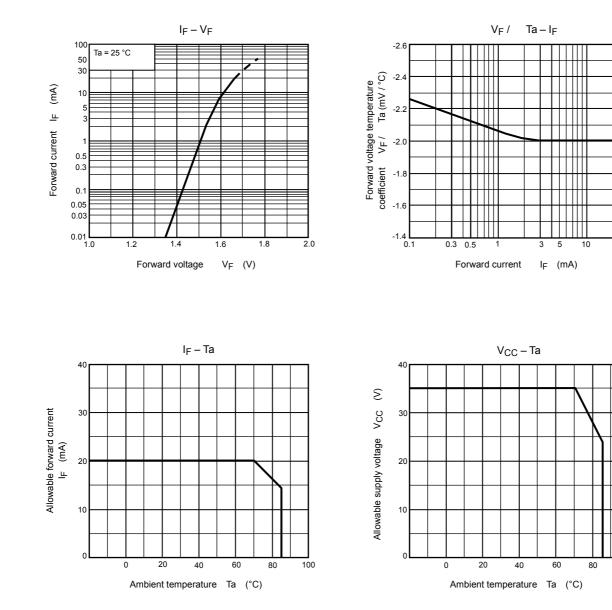


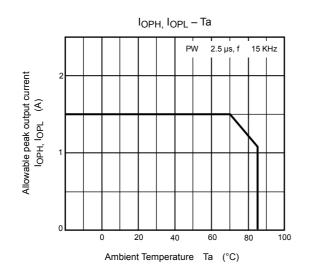
C_{ML}(C_{MH}) is the maximum rate of rise (fall) of the common mode voltage that can be sustained with the output voltage in the low (high) state.

TOSHIBA

30

100





RESTRICTIONS ON PRODUCT USE

- The information contained herein is subject to change without notice.
- The information contained herein is presented only as a guide for the applications of our products. No responsibility is assumed by TOSHIBA for any infringements of patents or other rights of the third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of TOSHIBA or others.
- TOSHIBA is continually working to improve the quality and reliability of its products. Nevertheless, semiconductor devices in general can malfunction or fail due to their inherent electrical sensitivity and vulnerability to physical stress. It is the responsibility of the buyer, when utilizing TOSHIBA products, to comply with the standards of safety in making a safe design for the entire system, and to avoid situations in which a malfunction or failure of such TOSHIBA products could cause loss of human life, bodily injury or damage to property.

In developing your designs, please ensure that TOSHIBA products are used within specified operating ranges as set forth in the most recent TOSHIBA products specifications. Also, please keep in mind the precautions and conditions set forth in the "Handling Guide for Semiconductor Devices," or "TOSHIBA Semiconductor Reliability Handbook" etc..

- The TOSHIBA products listed in this document are intended for usage in general electronics applications (computer, personal equipment, office equipment, measuring equipment, industrial robotics, domestic appliances, etc.). These TOSHIBA products are neither intended nor warranted for usage in equipment that requires extraordinarily high quality and/or reliability or a malfunction or failure of which may cause loss of human life or bodily injury ("Unintended Usage"). Unintended Usage include atomic energy control instruments, airplane or spaceship instruments, transportation instruments, traffic signal instruments, combustion control instruments, medical instruments, all types of safety devices, etc.. Unintended Usage of TOSHIBA products listed in this document shall be made at the customer's own risk.
- The products described in this document are subject to the foreign exchange and foreign trade laws.
- TOSHIBA products should not be embedded to the downstream products which are prohibited to be produced and sold, under any law and regulations.
- GaAs(Gallium Arsenide) is used in this product. The dust or vapor is harmful to the human body. Do not break, cut, crush or dissolve chemically.